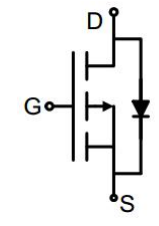
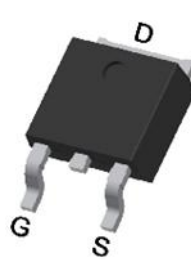


P-Channel Enhancement Mode Power MOSFET

<p>Description</p> <p>The G20P06K uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a widevariety of applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● V_{DS} -60V ● I_D (at $V_{GS} = -10V$) -20A ● $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 45mΩ ● 100% Avalanche Tested ● RoHS Compliant <p>Application</p> <ul style="list-style-type: none"> ● Power switch ● DC/DC converters 		 <p>Schematic diagram</p>  <p>TO-252</p>	
Device	Package	Marking	Packaging
G20P06K	TO-252	G20P06	2500pcs/Reel

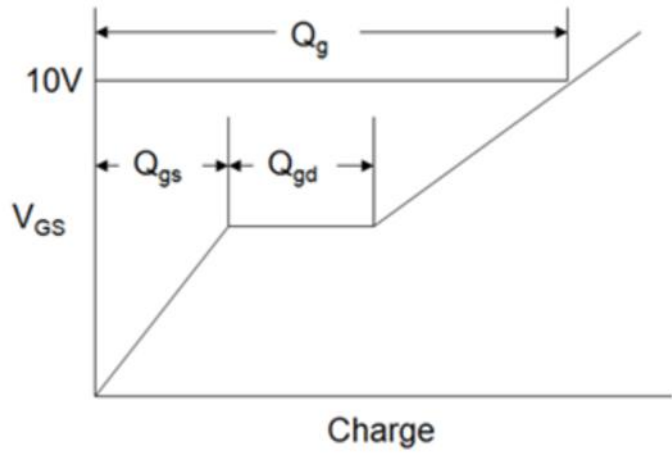
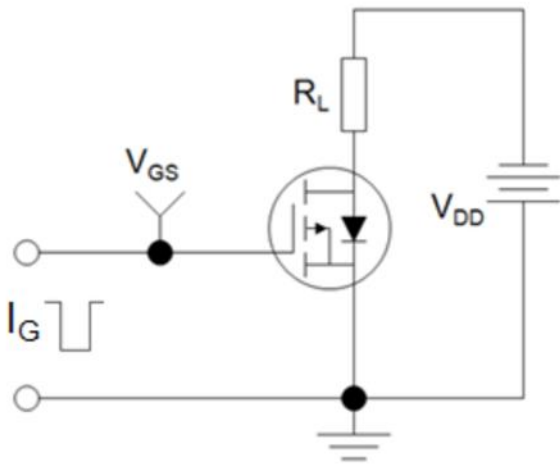
Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Continuous Drain Current	I_D	-20	A
Pulsed Drain Current (note1)	I_{DM}	-60	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	90	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	°C
Single pulse avalanche energy (note3)	E_{AS}	56	mJ
Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.4	°C/W

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-2	-2.6	-3.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -12A$	--	31	45	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=-12A$	--	25	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = -30V,$ $f = 1.0MHz$	--	3430	--	pF
Output Capacitance	C_{oss}		--	391	--	
Reverse Transfer Capacitance	C_{rss}		--	272	--	
Total Gate Charge	Q_g	$V_{DD} = -30V,$ $I_D = -20A,$ $V_{GS} = -10V$	--	46	--	nC
Gate-Source Charge	Q_{gs}		--	9.5	--	
Gate-Drain Charge	Q_{gd}		--	10.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -30V,$ $I_D = -20A,$ $R_G = 3\Omega$	--	12	--	ns
Turn-on Rise Time	t_r		--	15	--	
Turn-off Delay Time	$t_{d(off)}$		--	38	--	
Turn-off Fall Time	t_f		--	15	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	-25	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = -12A, V_{GS} = 0V$	--	--	-1.2	V
Reverse Recovery Time	T_{rr}	$I_S = -12A, V_{GS} = 0V$ $di/dt = -100A/\mu s$	--	47	--	ns

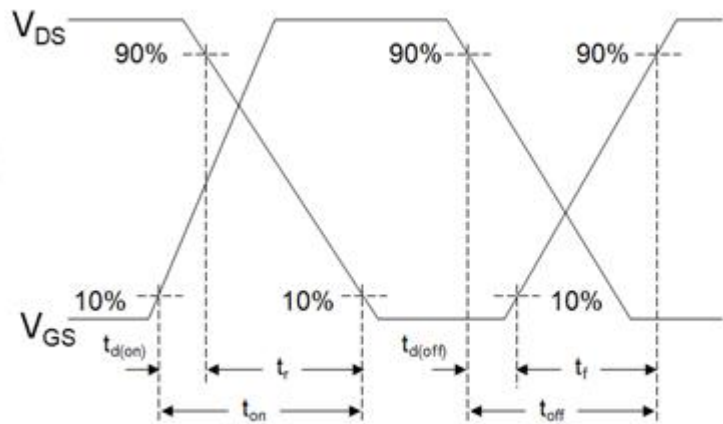
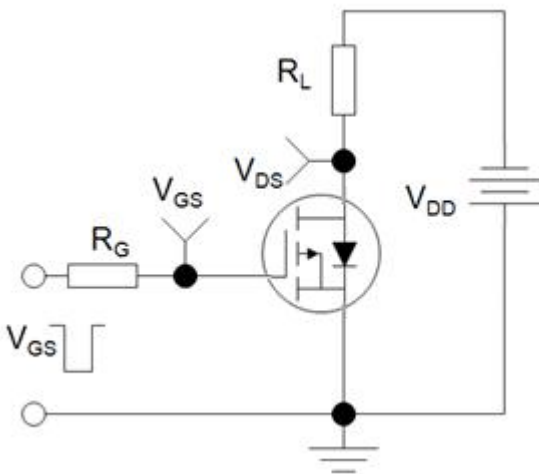
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25\Omega$

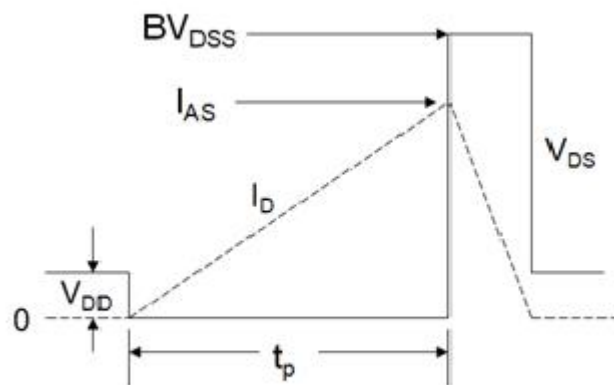
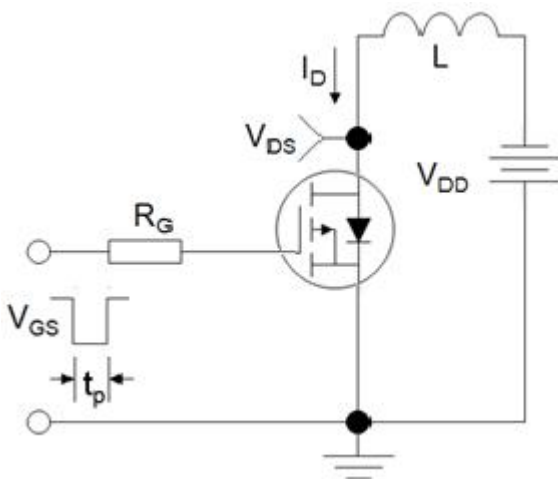
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

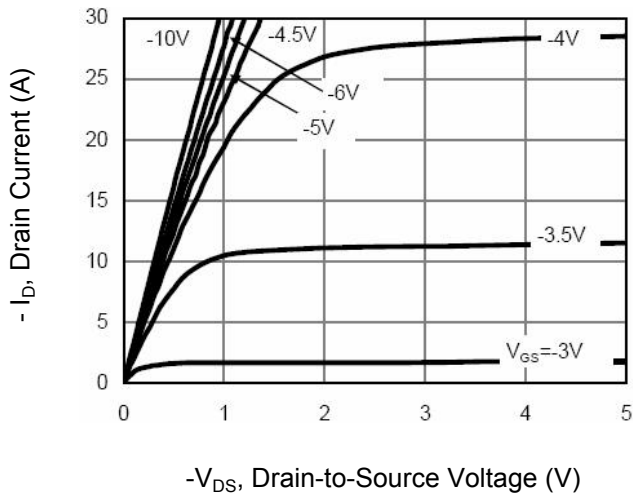


Figure 2. Transfer Characteristics

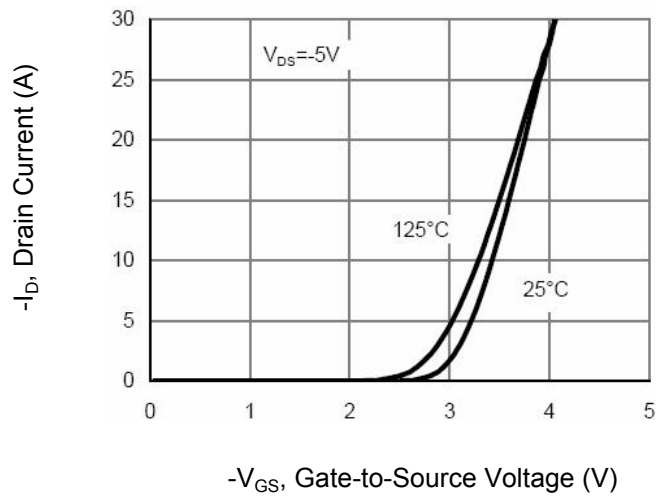


Figure 3. Gate Charge

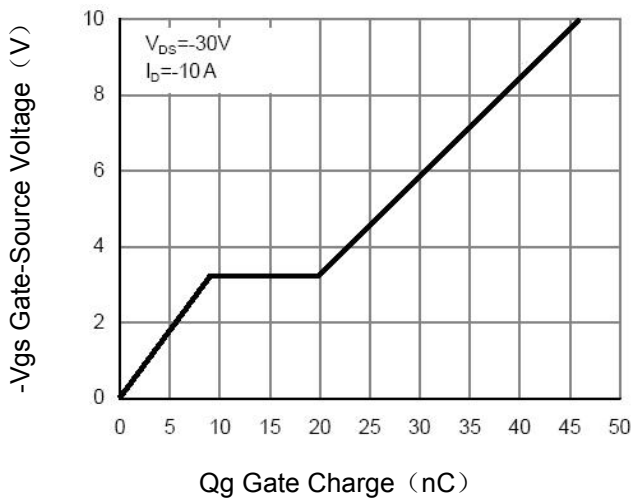


Figure 4. Drain Source On Resistance

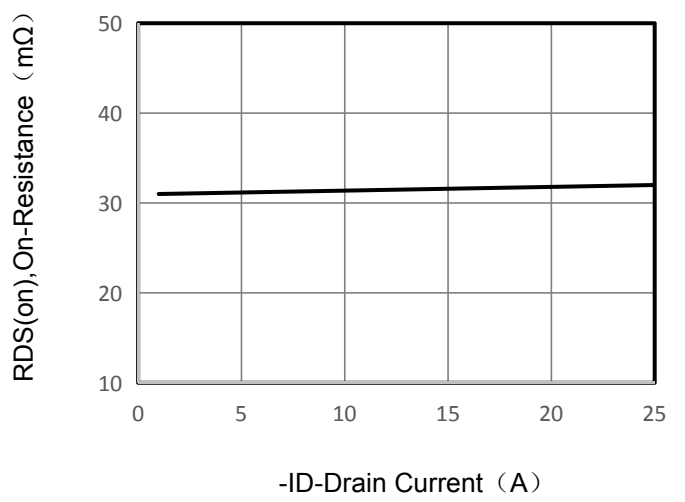


Figure 5. Capacitance

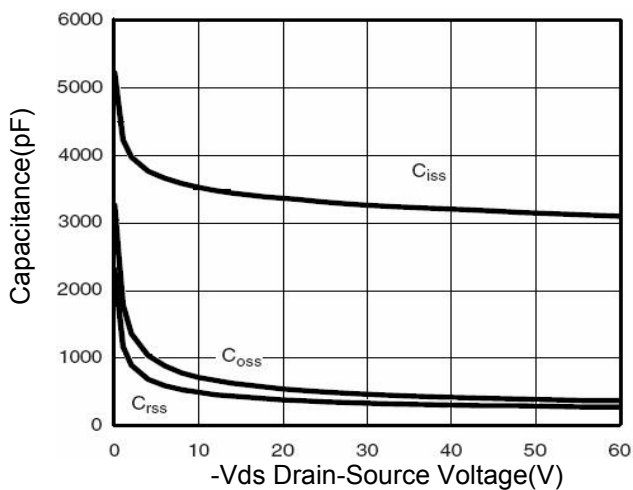
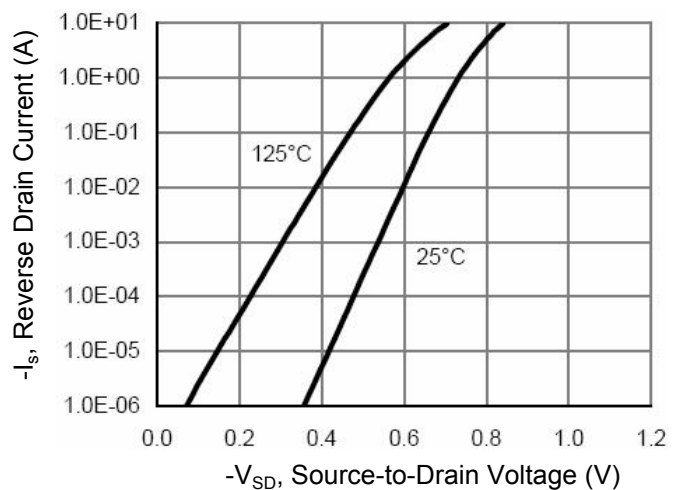


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

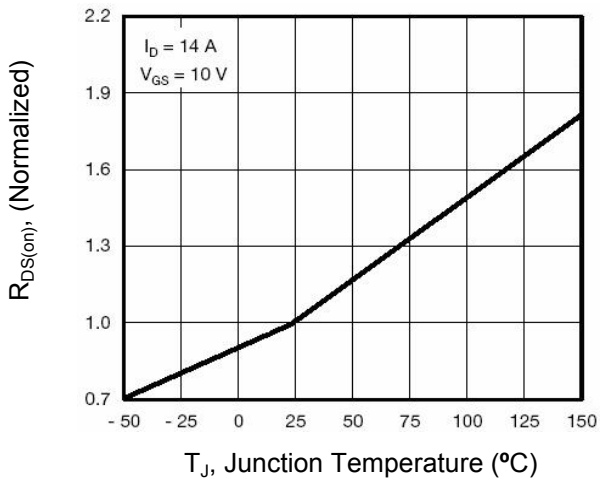


Figure 8. Safe Operation Area

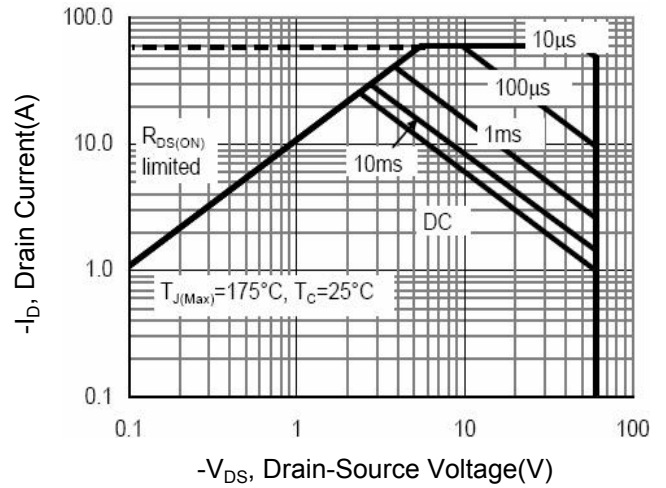
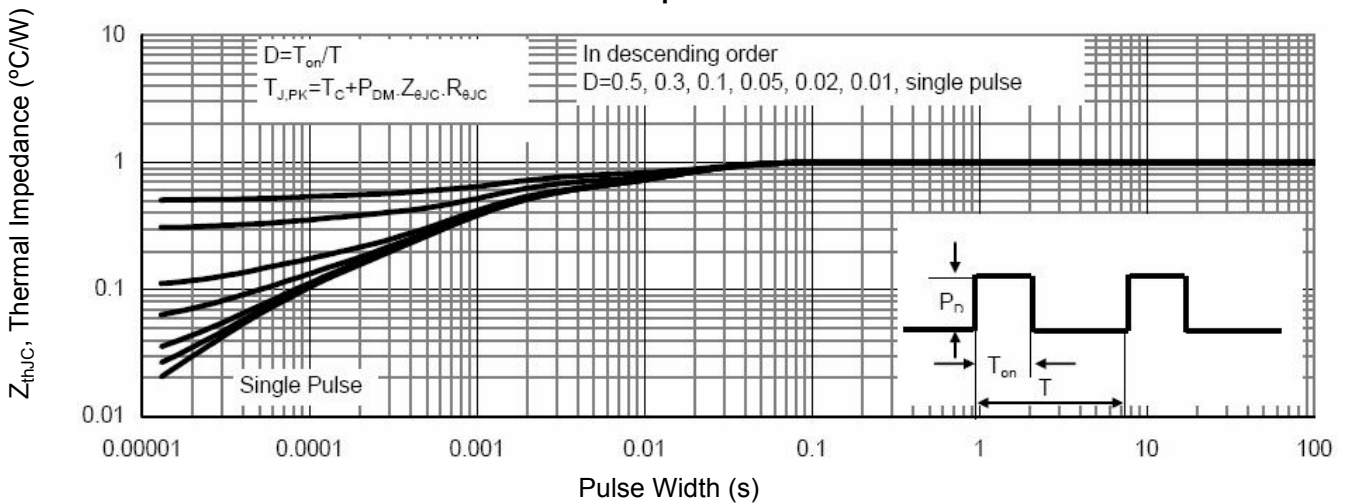
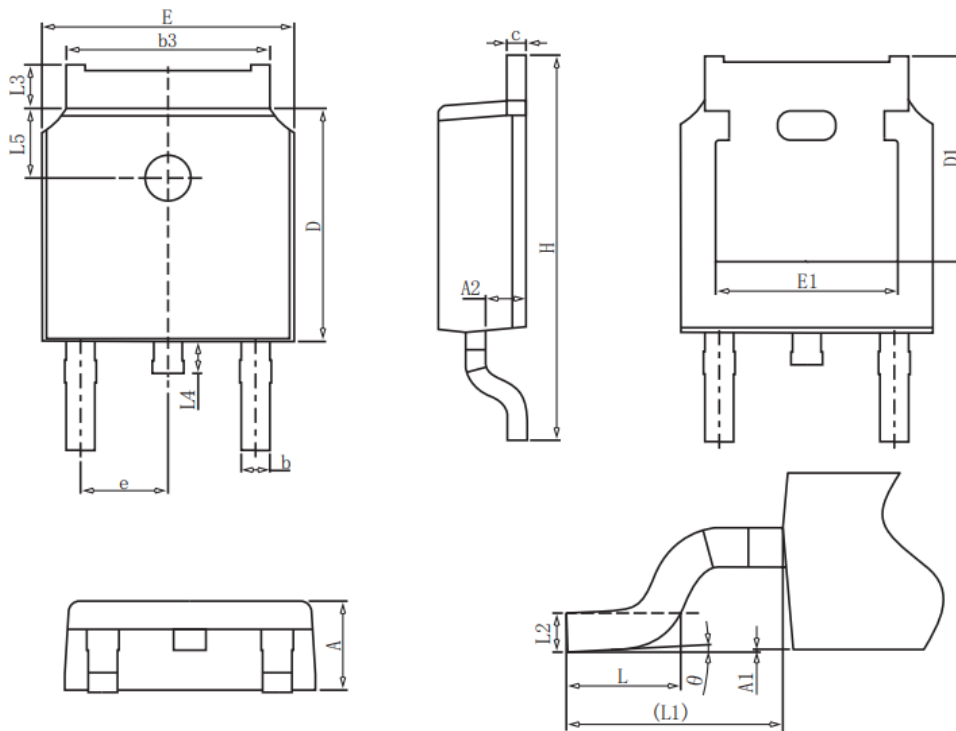


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.2	2.3	2.4
A1	0		0.2
A2	0.97	1.07	1.17
b	0.68	0.78	0.9
b3	5.2	5.33	5.5
c	0.43	0.53	0.63
D	5.98	6.1	6.22
D1	5.30REF		
E	6.4	6.6	6.8
E1	4.63		
e	2.286BSC		
H	9.4	10.1	10.5
L	1.38	1.5	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88		1.28
L4	0.5		1
L5	1.65	1.8	1.95
θ	0°		8°